

A1 a platen configured to orbit about an axis at a speed up to about 2000 revolutions per minute;

a polishing surface attached to the platen; and  
a workpiece carrier proximate the polishing surface.

2. The apparatus of claim 1, wherein the platen is configured to orbit at about 1000 orbits per minute.

A2 4. The apparatus of claim 1, wherein the platen orbits with an orbital radius of about 0.25 to about 1 inch.

12. A polishing system for removing material from a wafer surface, the wafer including low-k material, comprising:

A3 a plurality of polishing stations, wherein at least one of said plurality of polishing stations includes a platen configured to move at about 0.8 to about 3.2 meters per second relative to the wafer comprising low-k material;

a clean system including at least one clean station; and  
a load station.

25. A polishing system for removing conductive material deposited onto low-k material, comprising:

A4 a load and unload station;

a plurality of polishing stations, wherein at least one polishing station includes a platen configured to move relative to a workpiece comprising low-k material at about 0.8 to about 3.2 meters per second and a workpiece carrier configured to apply about 0.25 to about 2 psi to a workpiece in the direction of the platen; and

a clean system proximate the plurality of polishing station.

26. A method for removing material from a surface of a workpiece, including low-k material, comprising the steps of:

providing a workpiece comprising low-k material;

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placing the workpiece comprising low-k material in contact with a polishing surface; and  
orbiting the polishing surface at a speed about 500 to about orbits per minute.

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32. An apparatus for polishing a surface of a workpiece, the surface including a low dielectric constant material, comprising:

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a platen configured to move about an axis;

a polishing surface attached to the platen; and

a workpiece carrier proximate the polishing surface, wherein the platen and the workpiece carrier are configured such that the surface of the workpiece comprising a low dielectric constant material and the platen move at a relative speed of about 0.8 to about 3.2 meters per second.

33. A method for removing material from a surface of a workpiece, including low-k material, comprising the steps of:

providing a workpiece comprising low-k material;

placing the workpiece comprising low-k material in contact with a polishing surface; and

moving the polishing surface and the workpiece comprising low-k material relative to each other at a speed of about 0.8 to about 3.2 meters per second.

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#### REMARKS

In the August 1, 2002 Office Action, the Examiner rejected all pending claims 1-33. After entry of the foregoing amendments, claims 1-33 remain pending in the application.

#### 35 U.S.C. §112 Rejection

Claims 2 and 4 stand rejected under 35 U.S.C. §112, second paragraph, as being as being indefinite for failing to particularly point out and distinctly claim the subject matter that Applicants regard as the invention. Applicants have herein amended claims 2 and 4 to obviate this rejection and therefore request that the Examiner withdraw this rejection to claims 2 and 4.